**Product data sheet** 

## 1. Product profile

## 1.1. General description

NPN medium power transistors in a medium power SOT223 (SC73) Surface-Mounted Device (SMD) plastic package.

**Table 1. Product overview** 

| Type number | Package  |       | NPN comlement |
|-------------|----------|-------|---------------|
|             | Nexperia | JEDEC |               |
| BCP56T      | SOT223   | SC-73 | BCP53T        |
| BCP56-10T   |          |       | BCP53-10T     |
| BCP56-16T   |          |       | BCP53-16T     |

### 1.2. Features and benefits

- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- · Three current gain selections
- High power dissipation capability
- · AEC-Q101 qualified

## 1.3. Applications

- Linear voltage regulators
- MOSFET drivers
- · High-side switches
- Power management
- Amplifiers

### 1.4. Quick reference data

Table 2. Quick reference data

 $T_{amb}$  = 25 °C unless otherwise specified.

| Symbol          | Parameter                 | Conditions                          | Min | Тур | Max | Unit |
|-----------------|---------------------------|-------------------------------------|-----|-----|-----|------|
| $V_{CEO}$       | collector-emitter voltage | open base                           | -   | -   | 80  | V    |
| I <sub>C</sub>  | collector current         |                                     | -   | -   | 1   | А    |
| I <sub>CM</sub> | peak collector current    | single pulse; t <sub>p</sub> ≤ 1 ms | -   | -   | 2   | Α    |



## 80 V, 1 A NPN medium power transistors

| Symbol          | Parameter       | Conditions                                     |     | Min | Тур | Max | Unit |
|-----------------|-----------------|--|-----|-----|-----|-----|------|
| h <sub>FE</sub> | DC current gain |  |     |     |     |     |      |
|                 | BCP56T          | V <sub>CE</sub> = 2 V; I <sub>C</sub> = 150 mA | [1] | 63  | -   | 250 |      |
|                 | BCP56-10T       |  | [1] | 63  | -   | 160 |      |
|                 | BCP56-16T       |  | [1] | 100 | -   | 250 |      |

<sup>[1]</sup> pulsed;  $t_p \le 300 \ \mu s$ ;  $\delta \le 0.02$ 

## 2. Pinning information

## Table 3. Pinning

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--------------------|----------------|
| 1   | В      | base        | 4                  | С              |
| 2   | С      | collector   |                    |                |
| 3   | E      | emitter     |                    | в              |
| 4   | С      | collector   | ∃1 ∃2 ∃3           | Ė              |
|     |        |             |                    | sym123         |

# 3. Ordering information

### **Table 4. Ordering information**

| Type number | Package |   |         |
|-------------|---------|---|---------|
|             | Name    | Description   | Version |
| BCP56T      | SC-73   | plastic, surface-mounted package with increased heatsink; | SOT223  |
| BCP56-10T   |         | 4 leads   |         |
| BCP56-16T   |         |   |         |

# 4. Marking

### Table 5. Marking

| Type number | Marking code |
|-------------|--------------|
| BCP56T      | BCP56T       |
| BCP56-10T   | P5610T       |
| BCP56-16T   | P5616T       |

#### 80 V, 1 A NPN medium power transistors

## 5. Limiting values

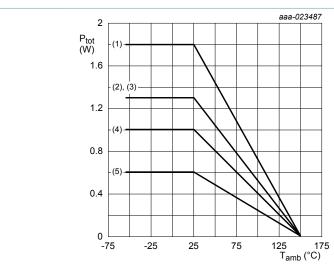
#### Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

T<sub>amb</sub> = 25 °C unless otherwise specified.

| Symbol           | Parameter                 | Conditions                          |     | Min | Max | Unit |
|------------------|---------------------------|-------------------------------------|-----|-----|-----|------|
| V <sub>CBO</sub> | collector-base voltage    | open emitter                        |     | -   | 100 | V    |
| V <sub>CEO</sub> | collector-emitter voltage | open base                           |     | -   | 80  | V    |
| V <sub>EBO</sub> | emitter-base voltage      | open collector                      |     | -   | 5   | V    |
| I <sub>C</sub>   | collector current         |                                     |     | -   | 1   | Α    |
| I <sub>CM</sub>  | peak collector current    | single pulse; t <sub>p</sub> ≤ 1 ms |     | -   | 2   | Α    |
| I <sub>B</sub>   | base current              |                                     |     | -   | 0.2 | Α    |
| I <sub>BM</sub>  | peak base current         | single pulse; t <sub>p</sub> ≤ 1 ms |     | -   | 0.3 | Α    |
| P <sub>tot</sub> | total power dissipation   | T <sub>amb</sub> ≤ 25 °C            | [1] | -   | 0.6 | W    |
|                  |                           |                                     | [2] | -   | 1   | W    |
|                  |                           |                                     | [3] | -   | 1.3 | W    |
|                  |                           |                                     | [4] | -   | 1.3 | W    |
|                  |                           |                                     | [5] | -   | 1.8 | W    |
| Tj               | junction temperature      |                                     |     | -   | 150 | °C   |
| T <sub>amb</sub> | ambient temperature       |                                     |     | -55 | 150 | °C   |
| T <sub>stg</sub> | storage temperature       |                                     |     | -65 | 150 | °C   |

- [1] Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated; mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated; mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on an FR4 Printed-Circuit-Board (PCB); 4-layer copper; tin-plated and standard footprint.
- [5] Device mounted on an FR4 Printed-Circuit-Board (PCB); 4-layer copper; tin-plated; mounting pad for collector 1 cm.<sup>2</sup>



- (1) FR4 PCB; 4-layer copper; 1 cm<sup>2</sup>
- (2) FR4 PCB; single-sided copper; 6 cm<sup>2</sup>
- (3) FR4 PCB; 4-layer copper; standard footprint
- (4) FR4 PCB; single-sided copper; 1 cm<sup>2</sup>
- (5) FR4 PCB; single-sided copper; standard footprint

#### Fig. 1. Power derating curves

## 80 V, 1 A NPN medium power transistors

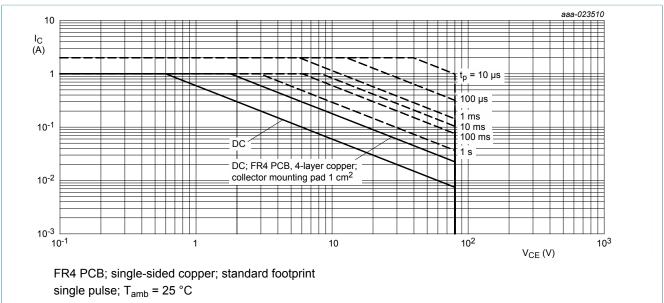


Fig. 2. Safe operating area; junction to ambient; continous and peak collector currents as a funtion of collecoremitter voltage

#### 80 V, 1 A NPN medium power transistors

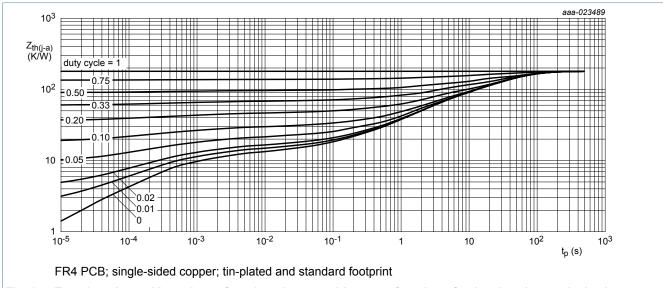
## 6. Thermal characteristics

#### **Table 7. Thermal characteristics**

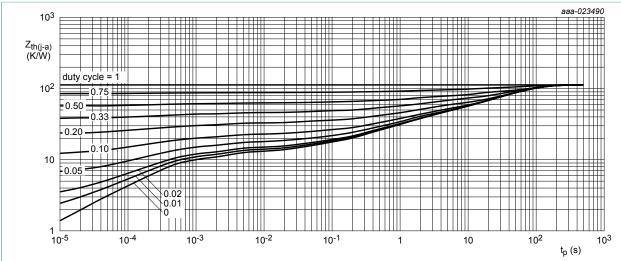
 $T_{amb}$  = 25 °C unless otherwise specified.

| Symbol               | Parameter  | Conditions  |     | Min | Тур | Max | Unit |
|----------------------|--|-------------|-----|-----|-----|-----|------|
| R <sub>th(j-a)</sub> | thermal resistance from junction to ambient      | in free air | [1] | -   | -   | 209 | K/W  |
|                      |  |             | [2] |     |     | 125 | K/W  |
|                      |  |             | [3] |     |     | 97  | K/W  |
|                      |  |             | [4] | -   | -   | 97  | K/W  |
|                      |  |             | [5] | -   | -   | 70  | K/W  |
| R <sub>(j-sp)</sub>  | thermal resistance from junction to solder point |             |     | -   | -   | 18  | K/W  |

- Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated and standard footprint.
- Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated; mounting pad for collector 1 cm<sup>2</sup>. Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated; mounting pad for collector 6 cm<sup>2</sup>. [3]
- Device mounted on an FR4 Printed-Circuit-Board (PCB); 4-layer copper; tin-plated and standard footprint. [4]
- [5] Device mounted on an FR4 Printed-Circuit-Board (PCB); 4-layer copper; tin-plated; mounting pad for collector 1 cm<sup>2</sup>.

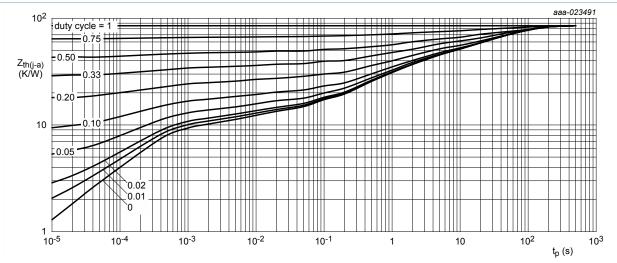


#### 80 V, 1 A NPN medium power transistors



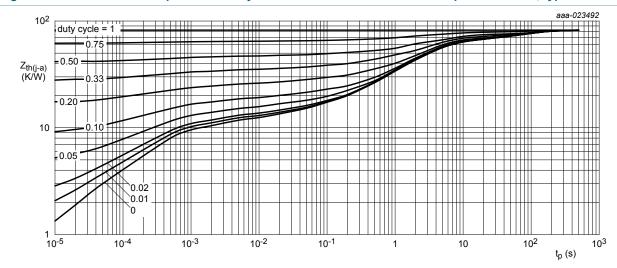
FR4 PCB; single-sided copper; tin-plated; mounting pad for collector 1 cm<sup>2</sup>

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB; single-sided copper; tin-plated; mounting pad for collector 6 cm<sup>2</sup>

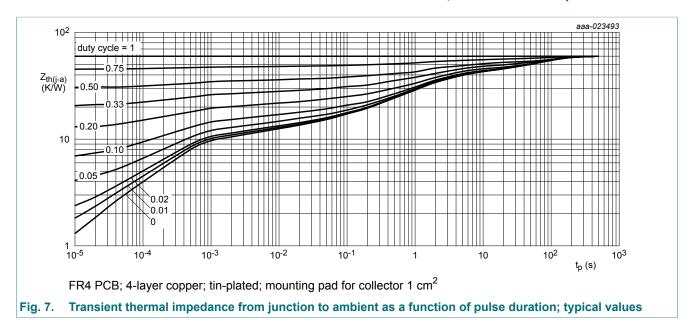
Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB; 4-layer copper; tin-plated and standard footprint

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 80 V, 1 A NPN medium power transistors



## 7. Characteristics

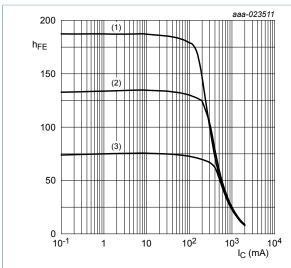
#### **Table 8. Characteristics**

 $T_{amb}$  = 25 °C unless otherwise specified.

| Symbol             | Parameter                            | Conditions   |     | Min | Тур | Max | Unit |
|--------------------|--------------------------------------|--|-----|-----|-----|-----|------|
| $V_{(BR)CBO}$      | collector-base<br>breakdown voltage  | I <sub>C</sub> = 100 μA; I <sub>E</sub> = 0 A                        |     | 100 | -   | -   | V    |
| $V_{(BR)CEO}$      | collector-emitter breakdown voltage  | I <sub>C</sub> = 2 mA; I <sub>E</sub> = 0 A                          |     | 80  | -   | -   | V    |
| $V_{(BR)EBO}$      | emitter-base<br>breakdown voltage    | I <sub>E</sub> = 100 μA; I <sub>C</sub> = 0 A                        |     | 5   | -   | -   | V    |
| I <sub>CBO</sub>   | collector-base                       | V <sub>CB</sub> = 30 V; I <sub>E</sub> = 0 A                         |     | -   | -   | 100 | nA   |
|                    | cut-off current                      | $V_{CB} = 30 \text{ V}; I_{E} = 0 \text{ A}; T_{j} = 150 \text{ °C}$ |     | -   | -   | 10  | μΑ   |
| I <sub>EBO</sub>   | emitter-base cut-off current         | V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A                          |     | -   | -   | 100 | nA   |
| h <sub>FE</sub>    | DC current gain                      |  |     |     |     |     |      |
|                    | BCP56T, -10T, -16T                   | V <sub>CE</sub> = 2 V; I <sub>C</sub> = 5 mA                         |     | 63  | -   | -   |      |
|                    |                                      | V <sub>CE</sub> = 2 V; I <sub>C</sub> = 500 mA                       | [1] | 40  | -   | -   |      |
|                    | BCP56T                               | V <sub>CE</sub> = 2 V; I <sub>C</sub> = 150 mA                       | [1] | 63  | -   | 250 |      |
|                    | BCP56-10T                            | V <sub>CE</sub> = 2 V; I <sub>C</sub> = 150 mA                       | [1] | 63  | -   | 160 |      |
|                    | BCP56-16T                            | V <sub>CE</sub> = 2 V; I <sub>C</sub> = 150 mA                       | [1] | 100 | -   | 250 |      |
| V <sub>CEsat</sub> | collector-emitter saturation voltage | I <sub>C</sub> = 500 mA; I <sub>B</sub> = 50 mA                      | [1] | -   | -   | 500 | mV   |
| $V_{BE}$           | base-emitter voltage                 | V <sub>CE</sub> = 2 V; I <sub>C</sub> = 500 mA                       | [1] | -   | -   | 1   | V    |
| f <sub>T</sub>     | transition frequency                 | V <sub>CE</sub> = 5 V; I <sub>C</sub> = 50 mA; f = 100 MHz           |     | 100 | 155 | -   | MHz  |
| C <sub>c</sub>     | collector capacitance                | $V_{CB} = 10 \text{ V}; I_E = I_e = 0 \text{ A}; f = 1 \text{ MHz}$  |     | -   | 4.5 | -   | pF   |

[1] pulsed;  $t_p \le 300 \ \mu s; \ \delta \le 0.02$ 

#### 80 V, 1 A NPN medium power transistors



$$V_{CE} = 2 V$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 8. DC current gain as a function of collector current; typical values

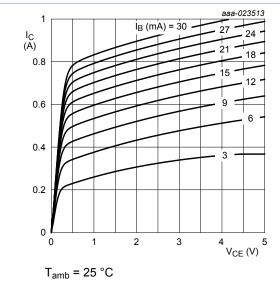
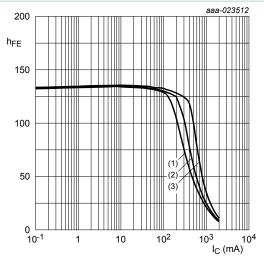


Fig. 10. Collector current as a function of collectoremitter voltage; typical values



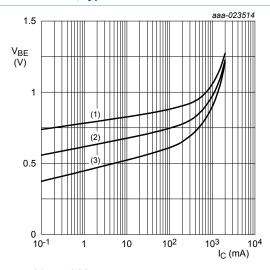
$$T_{amb} = 25 \, ^{\circ}C$$

(1) 
$$V_{CE} = 1 V$$

(2) 
$$V_{CE} = 2 V$$

(3) 
$$V_{CE} = 5 V$$

Fig. 9. DC current gain as a function of collector current; typical values



$$V_{CE} = 2 V$$

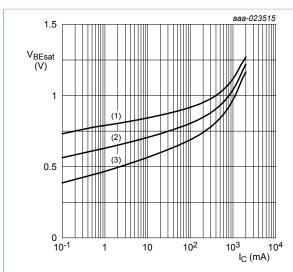
(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb}$$
 = 100 °C

Fig. 11. Base-emitter voltage as a function of collector current; typical values

### 80 V, 1 A NPN medium power transistors



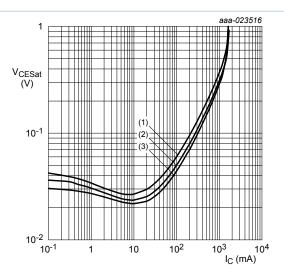
$$I_C/I_B = 10$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$





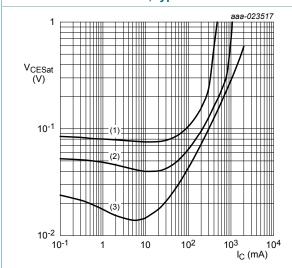
$$I_C/I_B = 10$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb}$$
 = -55 °C

function of collector current; typical values



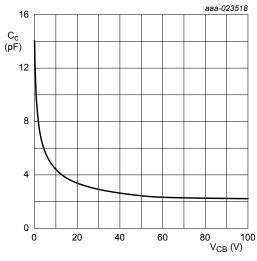
$$T_{amb}$$
 = 25 °C

(1) 
$$I_C/I_B = 50$$

(2) 
$$I_C/I_B = 20$$

(3) 
$$I_C/I_B = 5$$

Fig. 14. Collector-emitter saturation voltage as a function of collector current; typical values

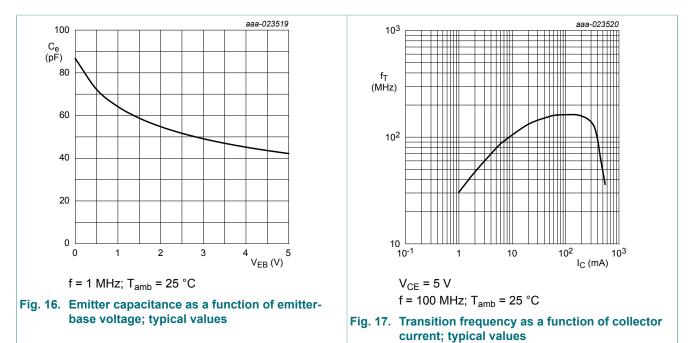


 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$ 

Fig. 15. Collector capacitance as a function of collectorbase voltage; typical values

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#### 80 V, 1 A NPN medium power transistors

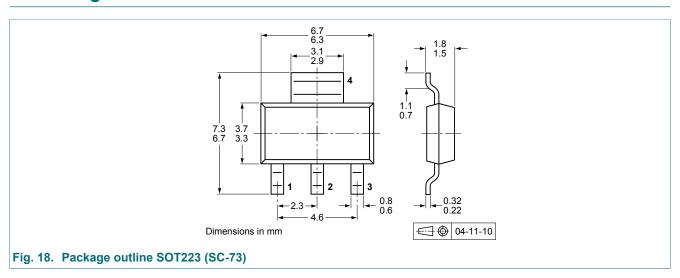


## 8. Test information

## 8.1. Quality information

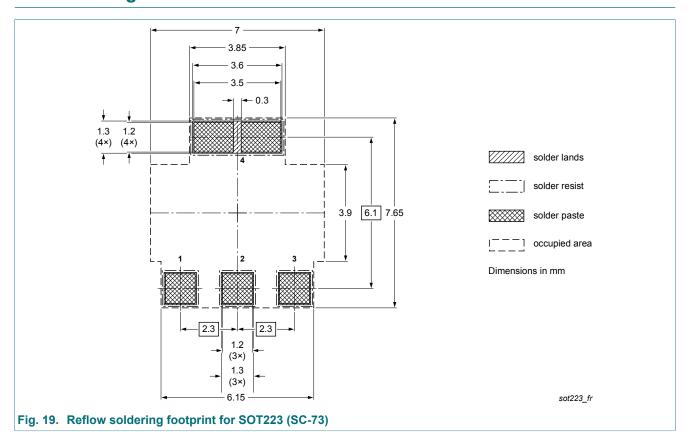
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

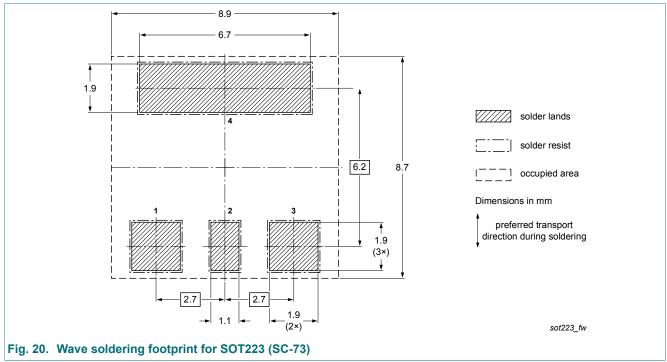
## 9. Package outline



### 80 V, 1 A NPN medium power transistors

# 10. Soldering





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## 80 V, 1 A NPN medium power transistors

# 11. Revision history

#### Table 9. Revision history

| Document ID    | Release date     | Data sheet status      | Change notice | Supersedes     |
|----------------|------------------|------------------------|---------------|----------------|
| BCP56T_SER v.2 | 20190429         | Product data sheet     | -             | BCP56T_SER v.1 |
| Modifications: | Characteristics: | breakdown voltages add | ed            |                |
| BCP56T_SER v.1 | 20160705         | Product data sheet     | -             | -              |

## 80 V, 1 A NPN medium power transistors

## 12. Legal information

#### **Data sheet status**

| Document status [1][2]         | Product<br>status [3] | Definition  |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet   | Development           | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification         | This document contains data from the preliminary specification.                       |
| Product [short]<br>data sheet  | Production            | This document contains the product specification.                                     |

- Please consult the most recently issued document before initiating or completing a design.
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Nexperia

# **BCP56T series**

## 80 V, 1 A NPN medium power transistors

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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 29 April 2019

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2N5769 2SC2412KT146S 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E
US6T6TR NJL0281DG 732314D CMXT3906 TR CPH3121-TL-E CPH6021-TL-H 873787E IMZ2AT108 UMX21NTR MCH6102-TL-E
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